

BUH1215

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- VERY HIGH SWITCHING SPEED

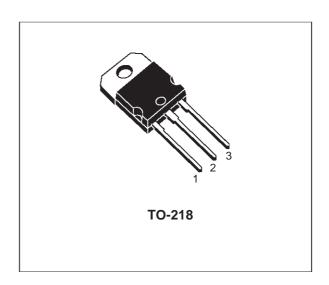
APPLICATIONS:

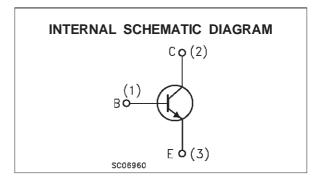
 HORIZONTAL DEFLECTION FOR COLOUR TV AND MONITORS

DESCRIPTION

The BUH1215 is manufactured using Multiepitaxial Mesa technology for cost-effective high performance and uses a Hollow Emitter structure to enhance switching speeds.

The BUH series is designed for use in horizontal deflection circuits in televisions and monitors.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	1500	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	700	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	10	V
Ic	Collector Current	16	Α
I _{CM}	Collector Peak Current (t _p < 5 ms)	22	Α
I _B	Base Current	9	Α
I _{BM}	Base Peak Current (t _p < 5 ms)	12	Α
P _{tot}	Total Dissipation at T _c = 25 °C	200	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

January 1999 1/7

BUH1215

THERMAL DATA

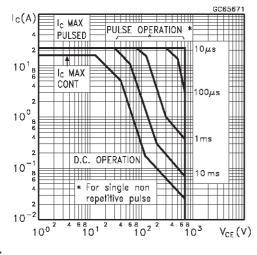
R _{thj-case} Thermal Resistance Junction-case	Max	0.63	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

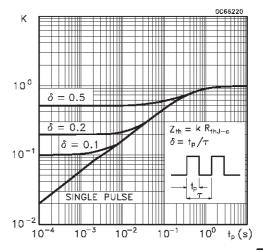
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V			0.2 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			100	μΑ
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 100 mA	700			V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	I _E = 10 mA	10			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 12 A I _B = 2.4 A			1.5	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 12 A I _B = 2.4 A			1.5	V
h _{FE} *	DC Current Gain	$I_{C} = 12 \text{ A}$ $V_{CE} = 5 \text{ V}$ $I_{C} = 12 \text{ A}$ $V_{CE} = 5 \text{ V}$ $T_{j} = 100 ^{\circ}\text{C}$	7 5	10	14	
t _s	RESISTIVE LOAD Storage Time Fall Time	$V_{CC} = 400 \text{ V}$ $I_{C} = 12 \text{ A}$ $I_{B1} = 2 \text{ A}$ $I_{B2} = -6 \text{ A}$		1.5 110		μs ns
t _s	INDUCTIVE LOAD Storage Time Fall Time			4 220		μs ns
t _s	INDUCTIVE LOAD Storage Time Fall Time	$\begin{aligned} &I_{C}=6 \text{ A} & f=64 \text{ KHz} \\ &I_{B1}=1 \text{ A} & V_{BE(off)}=-2 \text{ A} \\ &V_{ceflyback}=1200 \text{ sin}\bigg(\frac{\pi}{5} \cdot 10^6\bigg) t & V \end{aligned}$		3.5 180		μs ns

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area

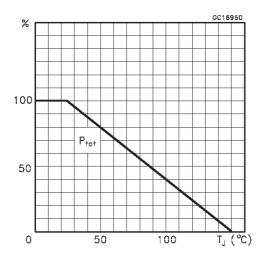


Thermal Impedance

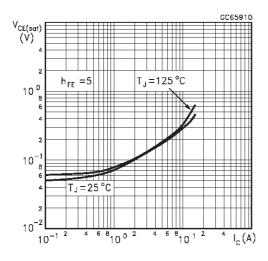


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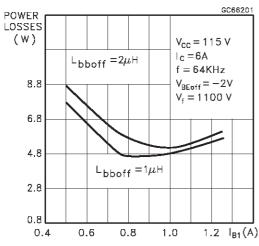
Derating Curve



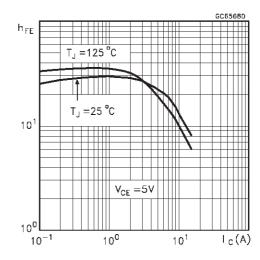
Collector Emitter Saturation Voltage



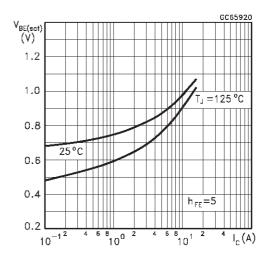
Power Losses at 64 KHz



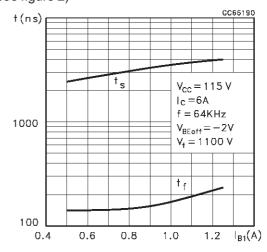
DC Current Gain



Base Emitter Saturation Voltage

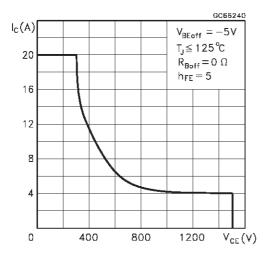


Switching Time Inductive Load at 64 KHz (see figure 2)



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Reverse Biased SOA



BASE DRIVE INFORMATION

In order to saturate the power switch and reduce conduction losses, adequate direct base current I_{B1} has to be provided for the lowest gain h_{FE} at 100 $^{\circ}$ C (line scan phase). On the other hand, negative base current I_{B2} must be provided the transistor to turn off (retrace phase).

Most of the dissipation, especially in the deflection application, occurs at switch-off so it is essential to determine the value of I_{B2} which minimizes power losses, fall time t_f and, consequently, T_j . A new set of curves have been defined to give total power losses, t_s and t_f as a function of I_{B1} at 64 KHz scanning frequencies for

choosing the optimum negative drive. The test circuit is illustrated in figure 1.

The values of L and C are calculated from the following equations:

$$\frac{1}{2}L(I_C)^2 = \frac{1}{2}C(V_{CEfly})^2$$
$$\omega = 2\pi f = \frac{1}{\sqrt{LC}}$$

Where I_C = operating collector current, V_{CEfly} = flyback voltage, f= frequency of oscillation during retrace.

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Figure 1: Inductive Load Switching Test Circuits.

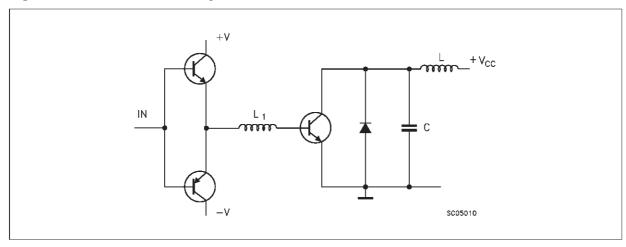
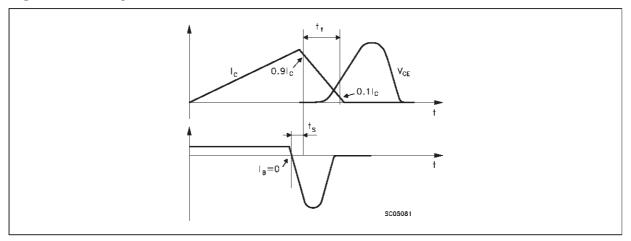
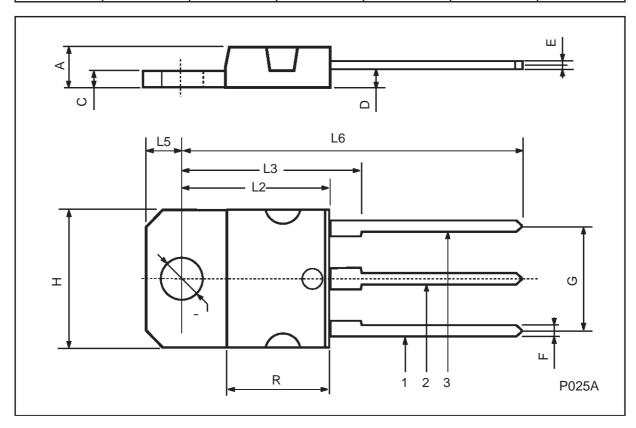


Figure 2: Switching Waveforms in a Deflection Circuit



TO-218 (SOT-93) MECHANICAL DATA

DIM.		mm			inch	
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	4.7		4.9	0.185		0.193
С	1.17		1.37	0.046		0.054
D		2.5			0.098	
Е	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
Н	14.7		15.2	0.578		0.598
L2	_		16.2	_		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	_		12.2	_		0.480
Ø	4		4.1	0.157		0.161



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